

AMENDMENTS TO THE CLAIMS

1-13. (Canceled)

14. (Currently amended) ~~The method for manufacturing a bipolar transistor as described in claim 9, further comprising the step of:~~ A method for manufacturing a bipolar transistor, the method comprising the steps of:

forming a base layer on an insulator, said base layer being in contact with a portion of a semiconductor substrate;

forming an insulating film on said base layer;

forming base and emitter electrode lead openings within said insulating film, said base electrode lead opening being formed simultaneous with said emitter electrode lead opening;

depositing a conducting film into said base electrode lead opening and into said emitter electrode lead opening, said conducting film within said base electrode lead opening being a base electrode lead portion and said conducting film within said emitter electrode lead opening being an emitter electrode lead portion; thereafter,

polishing said conducting film to separate said base electrode lead portion from said emitter electrode lead portion; and

depositing a silicide onto a polished surface of said conducting film.

15. (Canceled)

16. (New) A method for manufacturing a bipolar transistor, the method comprising the steps of:

forming a base layer on an insulator, said base layer being in contact with a portion of a semiconductor substrate;

forming an insulating film on said base layer;

forming base and emitter electrode lead openings within said insulating film, said base electrode lead opening being formed simultaneous with said emitter electrode lead opening;

depositing a conducting film into said base electrode lead opening and into said emitter electrode lead opening, said conducting film within said base electrode lead opening being a base electrode lead portion and said conducting film within said emitter electrode lead opening being an emitter electrode lead portion; thereafter,

polishing said conducting film to separate said base electrode lead portion from said emitter electrode lead portion; and

forming a silicide on a polished surface of said conducting film.

17. (New) The method for manufacturing a bipolar transistor as described in claim 16, wherein said insulator is on said semiconductor substrate, an opening within said insulator exposing said portion of the semiconductor substrate.

18. (New) The method for manufacturing a bipolar transistor as described in claim 16, wherein said base layer is a semiconductor material.

19. (New) The method for manufacturing a bipolar transistor as described in claim 16, wherein said conducting film is deposited simultaneously into said base and emitter electrode lead openings.

20. (New) The method for manufacturing a bipolar transistor as described in claim 16, further comprising the step of:

depositing an interlayer insulator onto said silicide and said insulating film.

21. (New) The method for manufacturing a bipolar transistor as described in claim 16, wherein said conducting film is a polysilicon film.

22. (New) The method for manufacturing a bipolar transistor as described in claim 16, wherein prior to the step of forming the silicide, the method further comprising the step of:

etching said polished surface of said conducting film.

23. (New) The method for manufacturing a bipolar transistor as described in claim 24, further comprising the step of:

diffusing a first dopant from said emitter electrode lead portion into said base layer to form an emitter region within said base layer.

24. (New) The method for manufacturing a bipolar transistor as described in claim 23, wherein prior to the step of forming the silicide, the method further comprising the step of:

forming an oxide on said polished surface of said conducting film.

25. (New) The method for manufacturing a bipolar transistor as described in claim 24, wherein prior to the step of forming the silicide, the method further comprising the steps of:

implanting said first dopant into said emitter electrode lead portion and implanting a second dopant into said base electrode lead portion, a conductivity of said second dopant being opposite to that of said first dopant; and thereafter,

removing said oxide from said polished surface of said conducting film.